

ABSTRACT

A nonvolatile memory device that makes it possible to improve the accuracy of screening testing while applying a voltage at or lower than the limit of the withstand voltage of an element for high voltage in the screening testing is provided. The nonvolatile memory device 51 comprises a high voltage production circuit 7 that produces a high voltage, a high voltage waveform conversion circuit 58 to which the high voltage is input and which converts the voltage waveform, and a memory cell section 2 provided with memory cells in which data rewriting is performed as a result of applying the converted high voltage. The high voltage waveform conversion circuit 58 comprises a test signal input section TEST and applies the high voltage input from the high voltage production circuit 7 to the memory cell section 2 without converting the voltage waveform when a test signal is input to the test signal input section.